

Amendments to the Specification

Please amend the following new paragraph on page 1, paragraph [0001] as follows.

[0001] The present application is a National Stage of International Application No. PCT/US03/11417, filed April 11, 2003, which claims priority of earlier filed provisional applications U.S. Application Nos. 60/372,263, entitled "ENHANCING SURFACE ROUGHNESS AFTER ELECTROPOLISHING," filed on April 12, 2002; No. 60/382,133, entitled "METHOD FOR REDUCING RECESS IN COPPER ELECTROPOLISHING," filed on May 21, 2002; No. 60/387,826, entitled "METHOD TO PLATE PLANAR METAL FILM ON SEMICONDUCTOR WAFERS," filed on June 8, 2002; No. 60/398,316, entitled "METHOD FOR REDUCING RECESS NON-UNIFORMITY ON PATTERNED TRENCH OR PAD AREA IN ELECTROPOLISHING PROCESS," filed on July 24, 2002, all of which are incorporated herein by reference in their entirety.